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Filing Date	August 30, 2000
First Named Inventor	Eugene P. Marsh
Group Art Unit	2811
Examiner Name	H. Vu
Attorney Docket Number	2269-4218US (99-0796.00/US)

U.S. PATENT DOCUMENTS					
Examiner Initials *	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
<i>V</i>		US-5,612,574	03/1997	Summerfelt et al.	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number	09/651,620
Filing Date	August 30, 2000
First Named Inventor	Eugene P. Marsh
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U.S. PATENT DOCUMENTS

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		Number - Kind Code² (if known)			
✓		US-4,250,210	02/1981	Crosby et al.	
		US- 4,982,309	01/1991	Shepherd	
		US-5,080,862	01/1992	Luthra	
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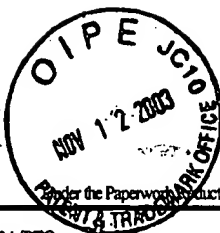
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Sheet 2 of 2

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Application Number	09/651,620
Filing Date	August 30, 2000
First Named Inventor	Eugene P. Marsh
Group Art Unit	2811
Examiner Name	H. Vu
Attorney Docket Number	2269-42181 US (99-0796 00/1 US)

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Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
✓		Cowles et al., Chemical Communications, p. 392, 1969.	
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